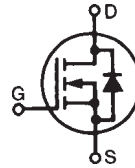


Trench™ Power MOSFETs

IXTH110N25T IXTV110N25TS

$$\begin{aligned} V_{DSS} &= 250V \\ I_{D25} &= 110A \\ R_{DS(on)} &\leq 24m\Omega \end{aligned}$$

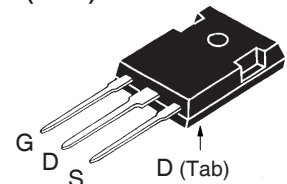
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



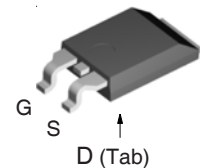
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	250	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	250	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	110	A
$I_{L(RMS)}$	External Lead Current Limit	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	300	A
I_A	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	1	J
P_D	$T_C = 25^\circ\text{C}$	694	W
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		+150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	1.6mm (0.063in) from Case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (to-247)	1.13/10	Nm/lb.in.
F_c	Mounting force (PLUS220SMD)	11..65/2.5..14.6	N/lb.
Weight	TO-247	6	g
	PLUS220SMD	4	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$			5 μA
	$T_J = 125^\circ\text{C}$			250 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Notes 1, 2			24 m Ω

TO-247 (IXTH)



PLUS220SMD(IXTV_S)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Avalanche Rated
- High Current Handling Capability
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	65	110	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		9400	pF
C_{oss}			850	pF
C_{rss}			55	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		19	ns
t_r			27	ns
$t_{d(off)}$			60	ns
t_f			27	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 25\text{A}$		157	nC
Q_{gs}			40	nC
Q_{gd}			50	nC
R_{thJC}		0.25		0.18°C/W
R_{thCS}				$^\circ\text{C/W}$

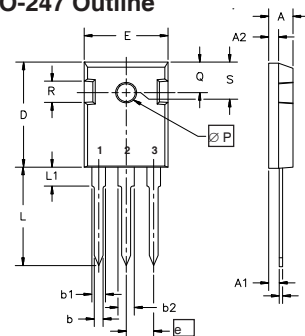
Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			110 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			350 A
V_{SD}	$I_F = 55\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.2 V
t_{rr}	$I_F = 55\text{A}$, $-di/dt = 250\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		170	ns
I_{RM}			27	A
Q_{RM}			2.3	μC

Notes:

- Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
- On through-hole package, $R_{DS(ON)}$ kelvin test contact location must be 5mm or less from the package body.

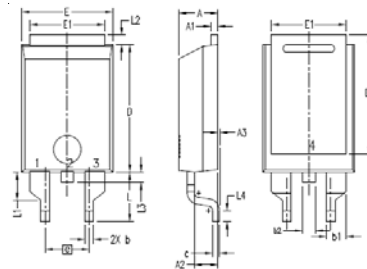
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

PLUS220SMD Outline



Terminals: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A ₁	.028	.035	0.70	0.90
A ₂	.098	.118	2.50	3.00
A ₃	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
b ₁	.080	.095	2.03	2.41
b ₂	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D ₁	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E ₁	.331	.346	8.40	8.80
e	.200BSC		5.08 BSC	
L	.209	.228	5.30	5.80
L ₁	.118	.138	3.00	3.50
L ₂	.035	.051	0.90	1.30
L ₃	.047	.059	1.20	1.50
L ₄	.039	.059	1.00	1.50

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

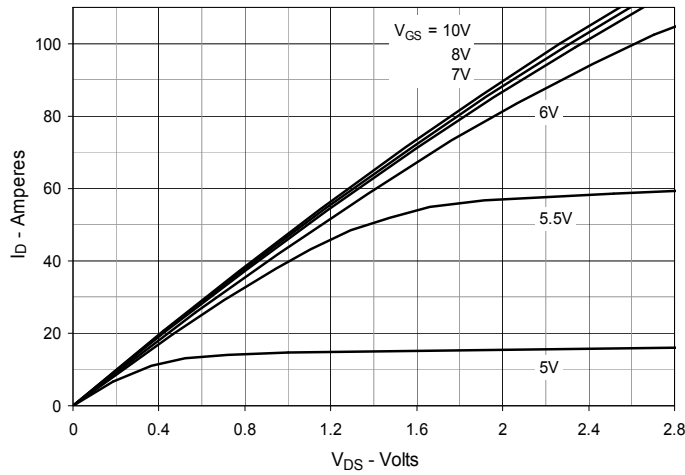


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

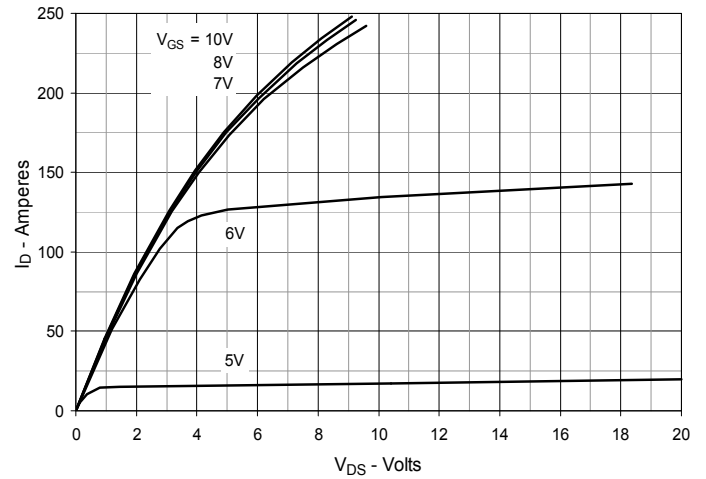


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

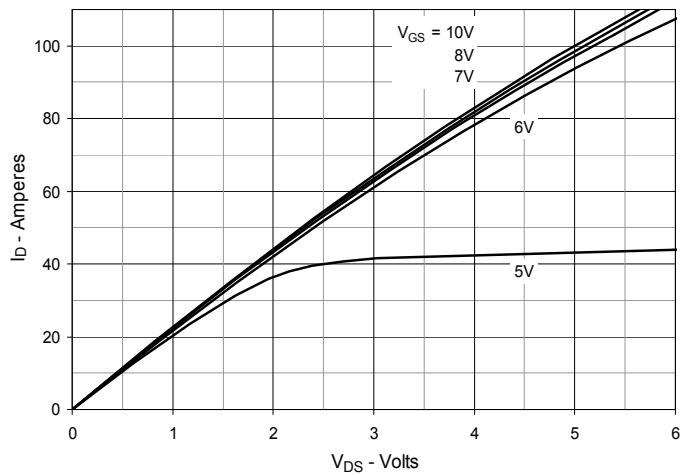


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Junction Temperature

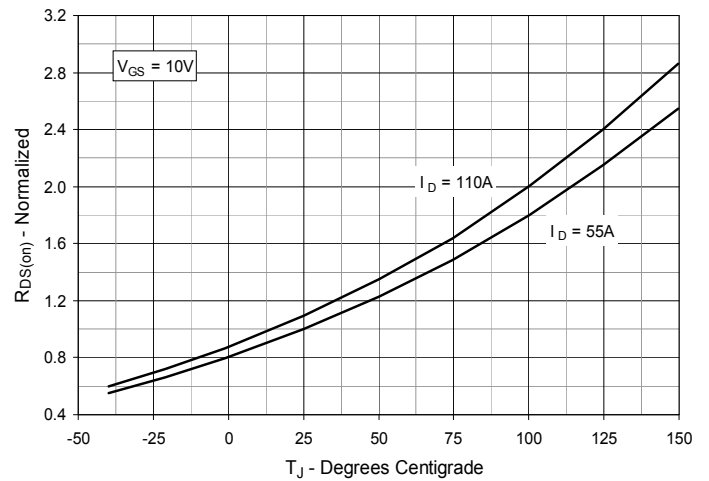


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Drain Current

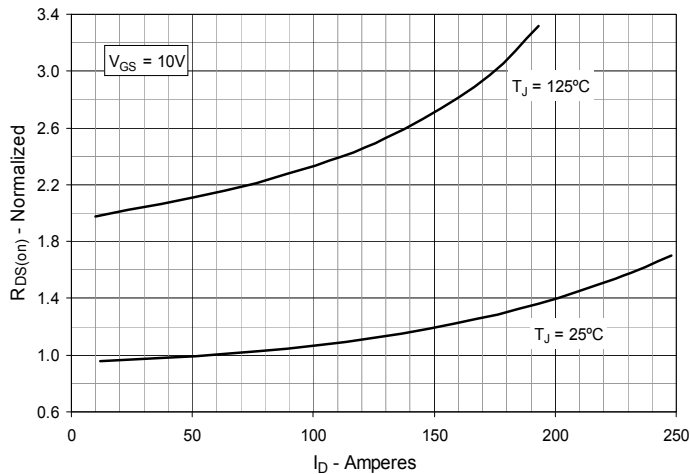


Fig. 6. Maximum Drain Current vs. Case Temperature

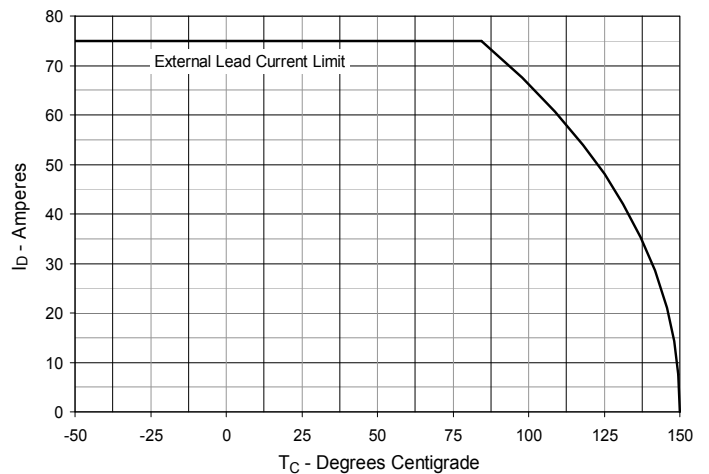


Fig. 7. Input Admittance

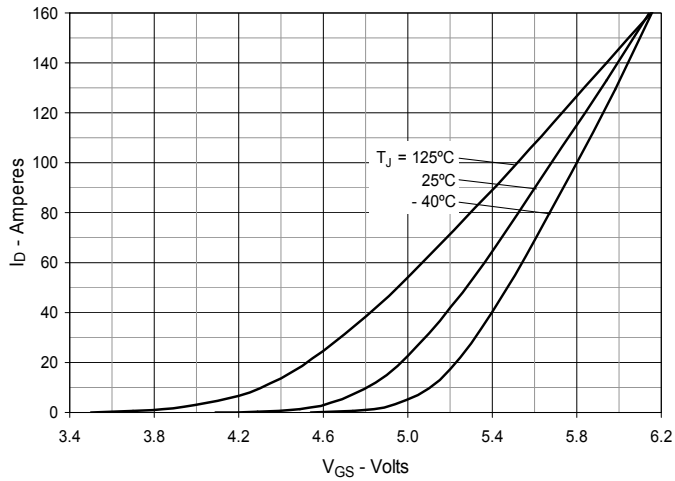


Fig. 8. Transconductance

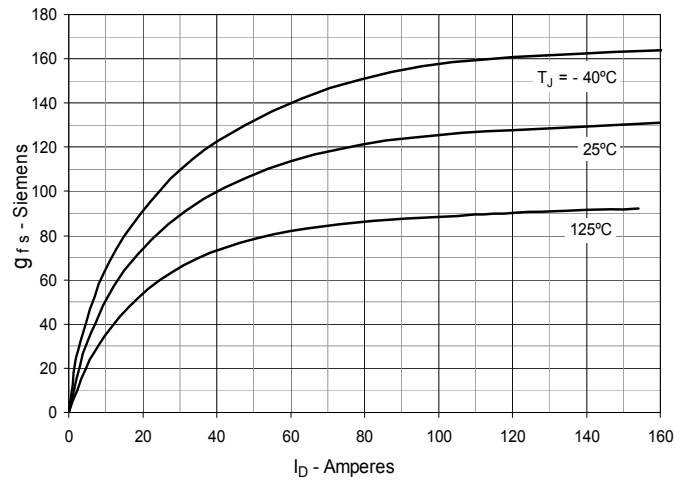


Fig. 9. Forward Voltage Drop of Intrinsic Diode

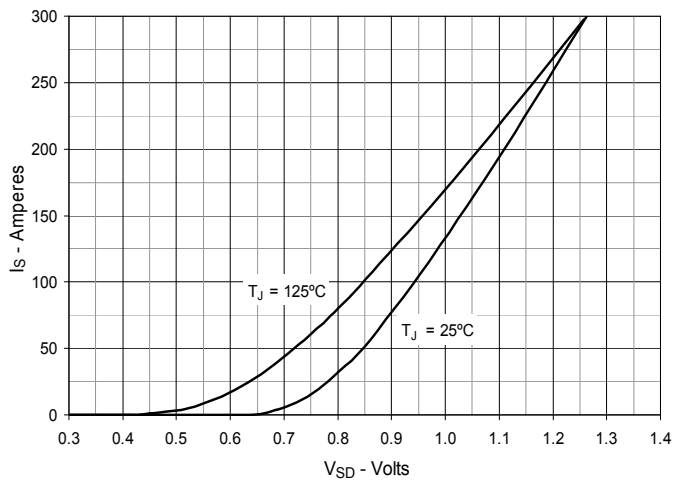


Fig. 10. Gate Charge

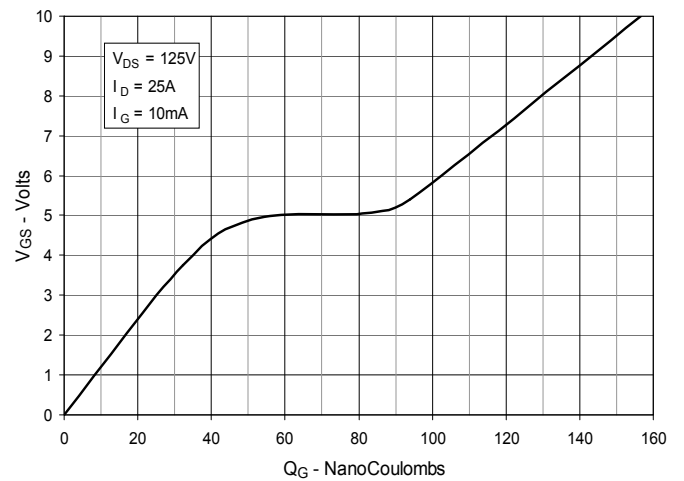


Fig. 11. Capacitance

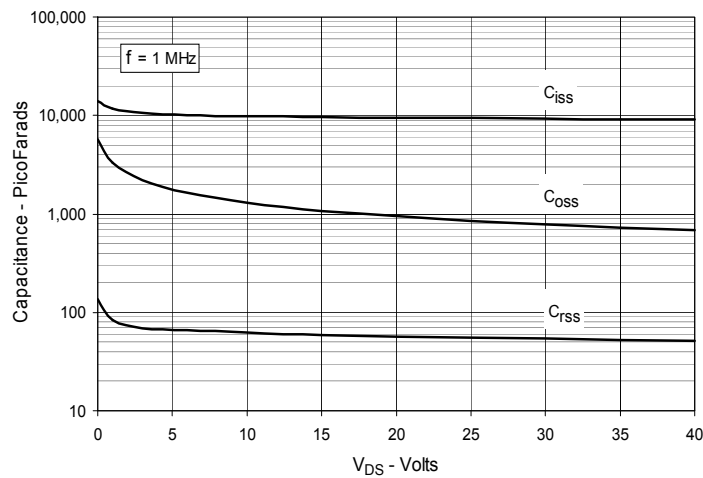


Fig. 12. Maximum Transient Thermal Impedance

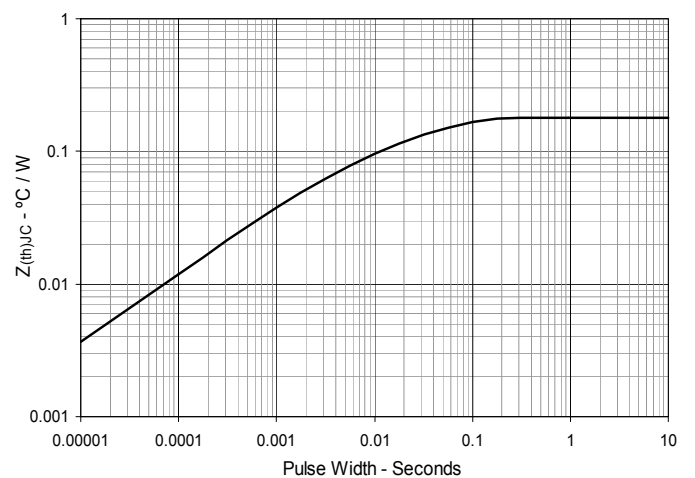


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

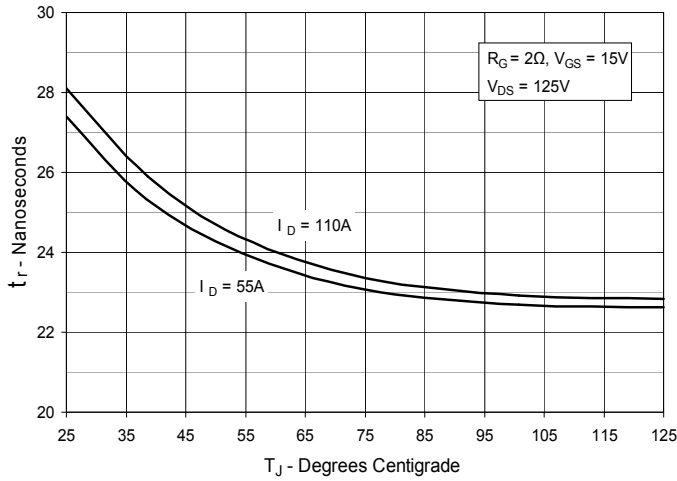


Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current

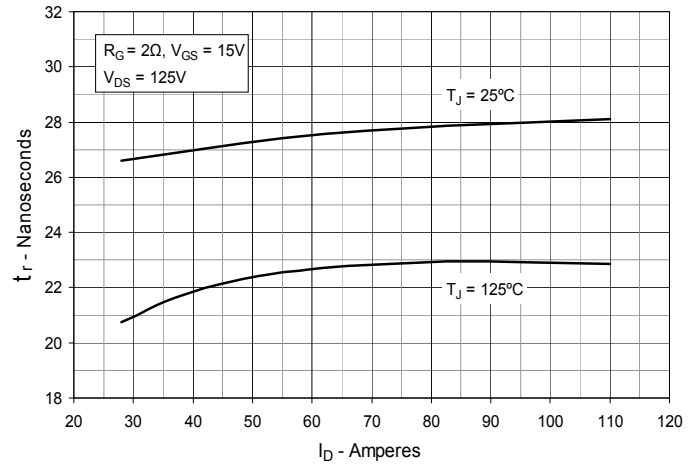


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

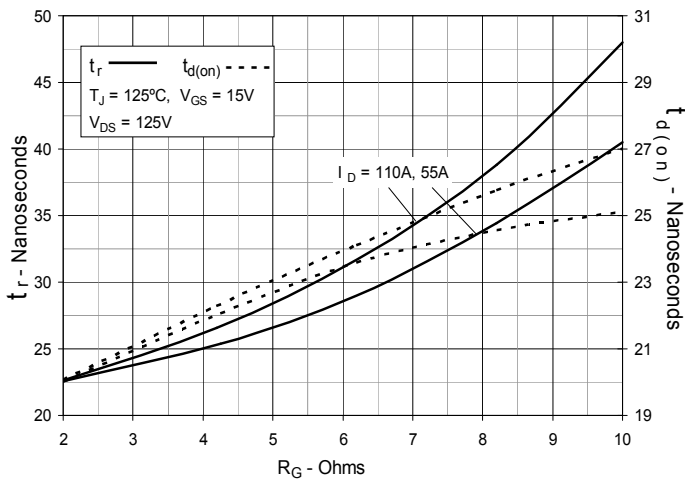


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

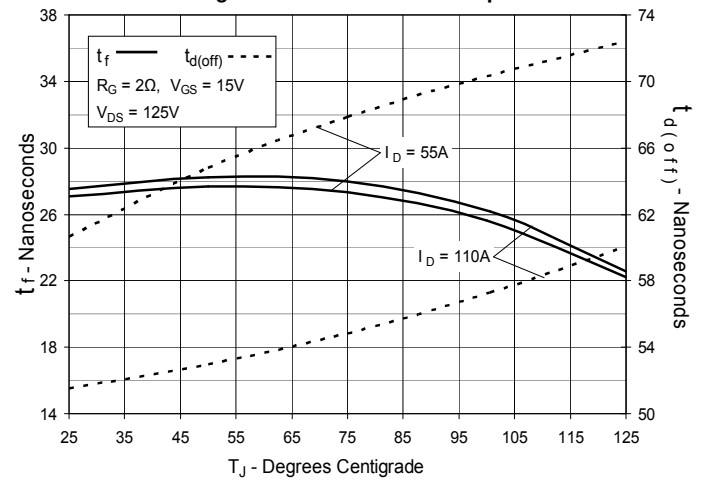


Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current

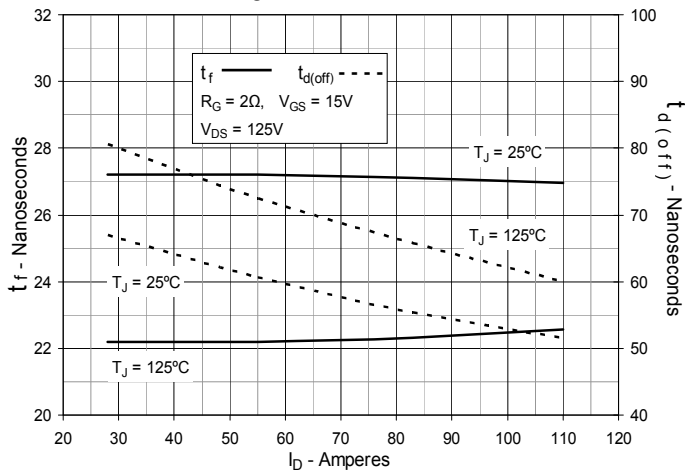


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

